

## 1KByte EEPROM IP with configuration 66p16w8bit

### OVERVIEW

130GF\_EEPROM\_04 is a nonvolatile electrically erasable programmable read-only memory (EEPROM) with volume 1056 Byte (8(bit per word) x 16(words per page) x 66(pages)) with parallel write&read data in one word.

Write EEPROM data comes to input DI<7:0> and write process execute if signal WR="1".

Data DI<7:0>, page address ADR\_P<6:0>, word address in page ADR\_W<3:0> are latched into internal registers and cannot be changed until the end of the writing process. At the end of the writing, the READY = "1" flag is set.

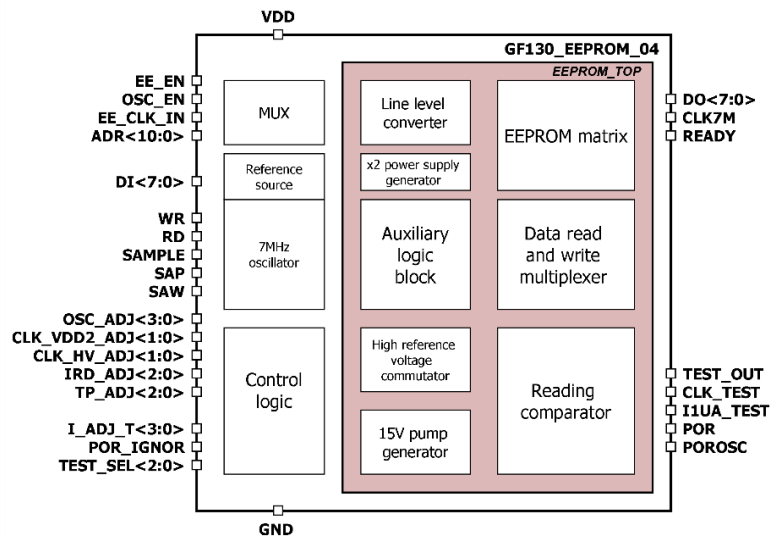
Data reading is carried out by specifying the page address ADR\_P<6:0> and the address of the word in the page ADR\_W<3:0>. After applying the reading strobe, the DO<7:0> signal is set at the output corresponding to the reading data from the corresponding addresses of the EEPROM cell.

EEPROM also has a 7MHz gated clock cell output (glitchless start) from a built-in oscillator. The oscillator has frequency control inputs to compensate for process variation. Memory is optimized for usage in the industrial and commercial applications, requiring low power consumption and supply voltage.

IP technology: Global Foundries Embedded EEPROM 0.13 um.

IP status: pre-silicon verification.

Total area: 0.226 mm<sup>2</sup>.



### ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Condition	Value			Unit
			min	typ.	max	
Supply voltage	V <sub>dd</sub>	–	1.1	1.2	1.3	V
Operating temperature range	T	–	-40	+27	+125	°C
EEPROM size	S	–	–	1	–	Kbyte
Output clock frequency	F <sub>clk</sub>	Adjustable	5.3	7.0	10.2	MHz
Frequency standard deviation	F <sub>σ</sub>	Mismatch + Process	–	9	–	%
Access time	t <sub>acc</sub>	–	–	115	300	ns
Time of writing process of one word	t <sub>wr</sub>	–	–	4.2	–	ms
Read setup time relative to read signal	t <sub>reads</sub>	–	20	–	–	us
Reference source current consumption	I <sub>CC_RS</sub>	–	2.3	3.6	6.2	uA
Oscillator current consumption	I <sub>CC_OSC</sub>	Not including I <sub>CC_RS</sub>	4.8	7.2	12.6	uA
Current consumption in read mode	I <sub>read</sub>	Including I <sub>CC_CL</sub> *; not including I <sub>CC_OSC</sub> , I <sub>CC_RS</sub>	14.0	22.0	41.0	uA
Average current consumption in write mode	I <sub>write_avg</sub>	Including I <sub>CC_CL</sub> *; not including I <sub>CC_OSC</sub> , I <sub>CC_RS</sub>	23.0	30.0	54.0	uA
Peak current consumption in write mode	I <sub>write_peak</sub>	Including I <sub>CC_CL</sub> *; not including I <sub>CC_OSC</sub> , I <sub>CC_RS</sub>	40.0	55.0	78.0	uA
Standby current	I <sub>standby</sub>	–	–	<0.05	<0.1	uA
Input logic-high level	V <sub>IH</sub>	For digital inputs	0.7*V <sub>dd</sub>	–	–	V
Input logic-low level	V <sub>IL</sub>		–	–	0.3	V

\*Note: I<sub>CC\_CL</sub> – Control Logic current consumption